Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIII)

SSM6K25FE

High Speed Switching Applications

· Optimum for high-density mounting in small packages

• Low on-resistance: $R_{on} = 395m\Omega \text{ (max) (@V_{GS} = 1.8 V)}$

 $R_{on} = 190 m\Omega \text{ (max) } (@V_{GS} = 2.5 \text{ V})$ $R_{on} = 145 m\Omega \text{ (max) } (@V_{GS} = 4.0 \text{ V})$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		V_{DS}	20	V	
Gate-Source voltage		V _{GSS}	± 12	V	
Drain current	DC	I _D	0.5	Α	
	Pulse	I _{DP}	1.5		
Drain power dissipation		P _D (Note 1)	500	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	−55~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

1.6±0.05 1.2±0.05 0.2 ± 0.05 1.6 ± 0.05 1.0 ± 0.05 6 5 0.12 ± 0.05 1,2,5,6 :Drain 3:Gate 4:Source ES6 **JEDEC** JEITA TOSHIBA 2-2N1A

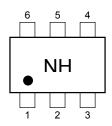
Weight: 3.0 mg (typ.)

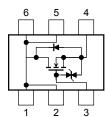
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on FR4 board. (25.4 mm \times 25.4 mm \times 1.6 t, Cu Pad: 645 mm 2)

Marking

Equivalent Circuit (top view)





Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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Electrical Characteristics (Ta = 25°C)

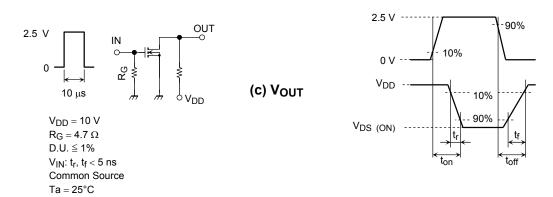
Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage curi	rent	I _{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$	_	_	±1	μА	
Drain-Source breakdown voltage		V (BR) DSS	$I_D = 1$ mA, $V_{GS} = 0$	20	_	_	V	
		V (BR) DSX	$I_D = 1 \text{ mA}, V_{GS} = -12 \text{ V}$	10	_	_	V	
Drain cut-off curre	ent	I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0$	_	_	1	μА	
Gate threshold vo	ltage	V _{th}	$V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$	0.5	_	1.1	V	
Forward transfer	admittance	Y _{fs}	$V_{DS} = 3 \text{ V}, I_D = 0.25 \text{ A}$ (No	e2) 1.2	2.4	_	S	
Drain-Source on-resistance		R _{DS} (ON)	$I_D = 0.25 \text{ A}, V_{GS} = 4.0 \text{ V}$ (No	e2) —	125	145	mΩ	
			$I_D = 0.25 \text{ A}, V_{GS} = 2.5 \text{ V}$ (No	e2) —	150	190		
			$I_D = 0.25 \text{ A}, V_{GS} = 1.8 \text{ V}$ (No	e2) —	200	395		
Input capacitance		C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		268	_	pF	
Reverse transfer capacitance C_{rss} $V_{DS} = 10 \text{ V}, V_{GS} = 0,$		$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	34	_	pF		
Output capacitance		Coss	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz		44	_	pF	
Switching time	Turn-on time	t _{on}	$V_{DD} = 10 \text{ V}, I_D = 0.25 \text{ A},$	_	11	_	no	
	Turn-off time	t _{off}	$V_{GS} = 0~2.5 \text{ V}, R_G = 4.7 \Omega$	_	15	_	ns	

Note2: Pulse test

Switching Time Test Circuit





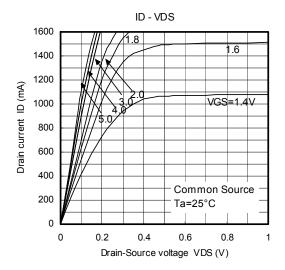


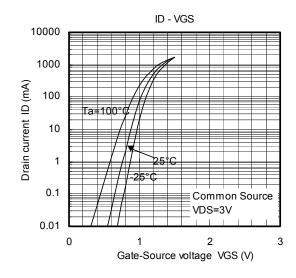
Precaution

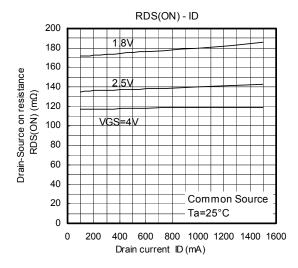
 V_{th} can be expressed as the voltage between gate and source when the low operating current value is ID=100 μ A for this product. For normal switching operation, V_{GS} (on) requires a higher voltage than V_{th} and V_{GS} (off) requires a lower voltage than V_{th} .

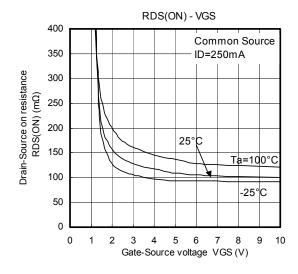
(The relationship can be established as follows: $V_{GS (off)} < V_{th} < V_{GS (on)}$)

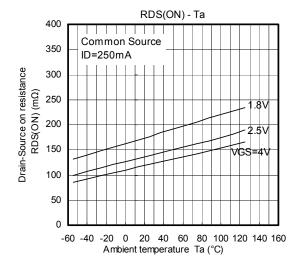
Please take this into consideration when using the device.

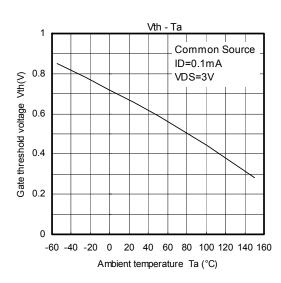




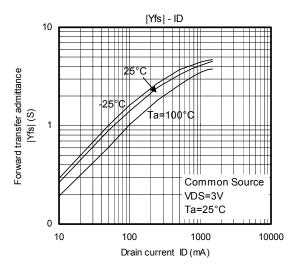


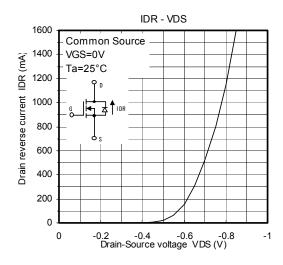


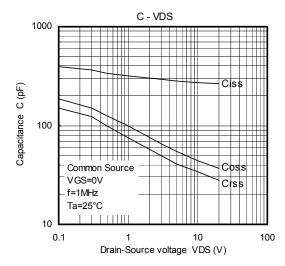


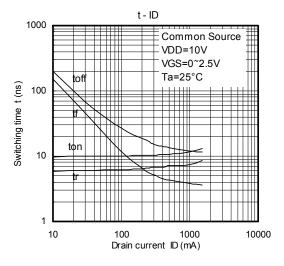


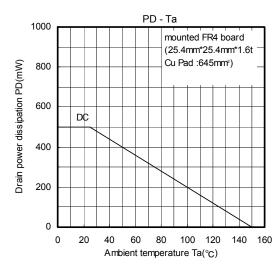
3 2007-11-01











4 2007-11-01

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5 2007-11-01